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Advanced Power MOSFET

FEATURES

■ Avalanche Rugged Technology

■ Rugged Gate Oxide Technology

■ Lower Input Capacitance

■ Improved Gate Charge

■ Extended Safe Operating Area

■ 175°C Operating Temperature

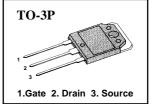
■ Lower Leakage Current : 10 μ A (Max.) @ $V_{DS} = 100V$

■ Lower $R_{DS(ON)}$: 0.032 Ω (Typ.)

$$BV_{DSS} = 100 V$$

$$R_{DS(on)} = 0.04 \Omega$$

$$I_D = 43 A$$



Absolute Maximum Ratings

Symbol	Characteristic	Value	Units	
V _{DSS}	Drain-to-Source Voltage	100	V	
	Continuous Drain Current (T _C =25°C)	43		
I _D	Continuous Drain Current (T _C =100 °C)	30.4	A
I _{DM}	Drain Current-Pulsed	0	170	Α
V_{GS}	Gate-to-Source Voltage	<u>+</u> 2 0	٧	
E _{AS}	Single Pulsed Avalanche Energy	2	740	mJ
I _{AR}	Avalanche Current	0	43	Α
E _{AR}	Repetitive Avalanche Energy	0	19.3	mJ
dv/dt	Peak Diode Recovery dv/dt	3	6.5	V/ns
Б	Total Power Dissipation (T _C =25°C)		193	W
P_{D}	Linear Derating Factor		1.28	W/°C
	Operating Junction and	FF to 147F		
T_J , T_STG	Storage Temperature Range	- 55 to +175		
	Maximum Lead Temp. for Soldering	200	°C	
T _L	Purposes, 1/8" from case for 5-seco	300		

Thermal Resistance

Symbol	Characteristic	Тур.	Max.	Units
R _{θJC}	Junction-to-Case		0.78	
R _{ecs}	Case-to-Sink	0.24		°C/W
R _{θJA}	Junction-to-Ambient		40	

Electrical Characteristics (T_C =25 $^{\circ}$ C unless otherwise specified)

Symbol	Characteristic	Min.	Тур.	Max.	Units	Test Condition
BV _{DSS}	Drain-Source Breakdown Voltage	100		1	V	V_{GS} =0V, I_{D} =250 μ A
Δ BV/ Δ T $_{ m J}$	Breakdown Voltage Temp. Coeff.		0.11	1	V/°C	I _D =250μA See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	2.0		4.0	٧	V_{DS} =5 V , I_{D} =250 μ A
1	Gate-Source Leakage, Forward			100	nA	V _{GS} =20V
I _{GSS}	Gate-Source Leakage, Reverse			-100	шА	V _{GS} =-20V
	Drain to Course Lackage Current			10		V _{DS} =100V
I _{DSS}	Drain-to-Source Leakage Current			100	μΑ	V_{DS} =80V, T_{C} =150°C
В	Static Drain-Source				Ω	V _{cs} =10V,I _D =21.5A ④
R _{DS(on)}	On-State Resistance			0.04	1 22	$V_{GS} = 10V, I_D = 21.5A$ 4
g _{fs}	Forward Transconductance		28.34	-	Ω	$V_{DS} = 40V, I_{D} = 21.5A$ 4
C _{iss}	Input Capacitance		1750	2270		$V_{GS}=0V, V_{DS}=25V, f=1MHz$
C _{oss}	Output Capacitance		420	485	pF	See Fig 5
C_{rss}	Reverse Transfer Capacitance		185	215		See Fig 5
t _{d(on)}	Turn-On Delay Time		17	50		V _{DD} =50V,I _D =40A,
t _r	Rise Time		20	50		
$t_{d(off)}$	Turn-Off Delay Time		80	160	ns	$R_G=6.2\Omega$
t _f	Fall Time		45	100		See Fig 13 ④⑤
Q_g	Total Gate Charge		75	97		$V_{DS} = 80V, V_{GS} = 10V,$
Q_{gs}	Gate-Source Charge		13.2	1	nC	I _D =40A
Q_gd	Gate-Drain("Miller") Charge		34.8			See Fig 6 & Fig 12 46

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic		Min.	Тур.	Max.	Units	Test Condition
I _S	Continuous Source Current				43	Α	Integral reverse pn-diode
I _{SM}	Pulsed-Source Current	0			170		in the MOSFET
V _{SD}	Diode Forward Voltage	4			1.6	V	$T_J = 25 ^{\circ}\text{C}, I_S = 43 \text{A}, V_{GS} = 0 \text{V}$
t _{rr}	Reverse Recovery Time			135		ns	T _J =25°C,I _F =40A
Q _{rr}	Reverse Recovery Charge			0.65		μC	$di_F/dt=100A/\mu s$

- Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 2 L=0.6mH, I $_{\rm AS}$ =43A, V $_{\rm DD}$ =25V, R $_{\rm G}$ =27 Ω , Starting T $_{\rm J}$ =25°C
- (3) $I_{SD} \le 40A$, di/dt $\le 470A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25$ °C (4) Pulse Test : Pulse Width = 250 μs , Duty Cycle $\le 2\%$
- **(5)** Essentially Independent of Operating Temperature



Fig 1. Output Characteristics

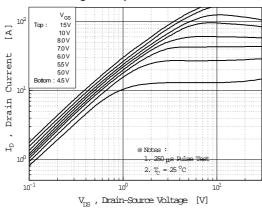


Fig 2. Transfer Characteristics

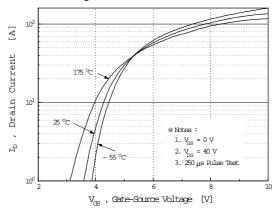


Fig 3. On-Resistance vs. Drain Current

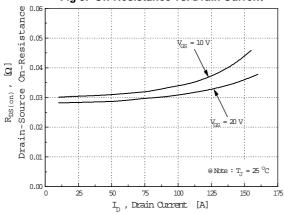


Fig 4. Source-Drain Diode Forward Voltage

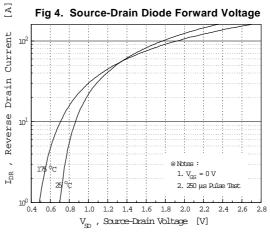


Fig 5. Capacitance vs. Drain-Source Voltage

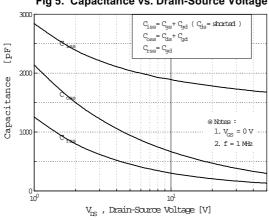
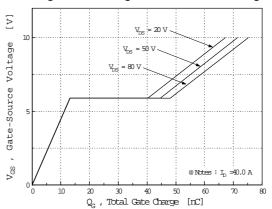
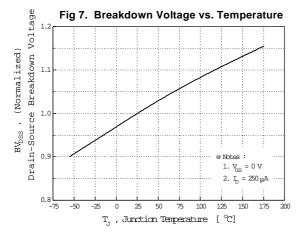


Fig 6. Gate Charge vs. Gate-Source Voltage





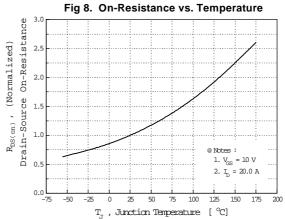
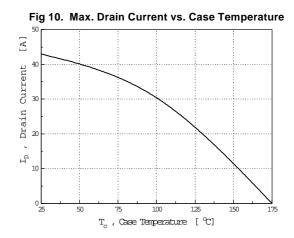


Fig 9. Max. Safe Operating Area [A] 10 $I_{\rm D}$, Drain Current 10¹ 10 1. $\rm T_{\rm C}$ = 25 $\rm ^{o}C$ 2. $T_J = 175$ °C 3. Single Pulse 10⁻¹

10¹

V_{DS} , Drain-Source Voltage [V]



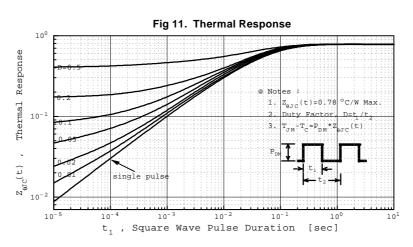




Fig 12. Gate Charge Test Circuit & Waveform

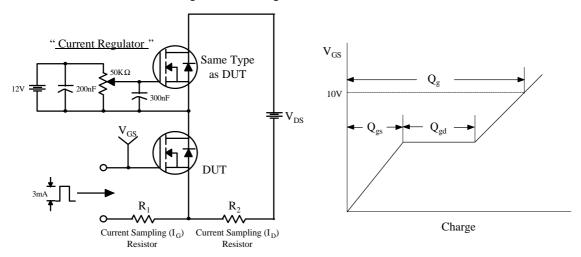


Fig 13. Resistive Switching Test Circuit & Waveforms

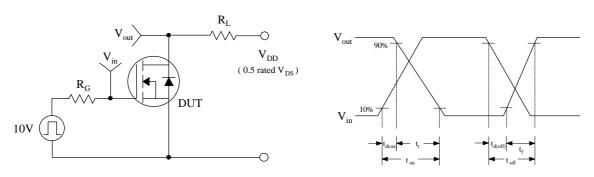


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

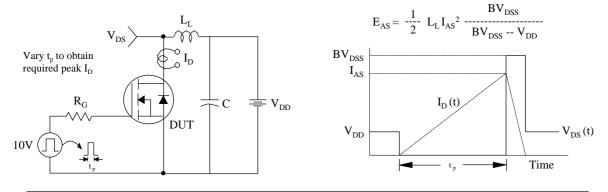
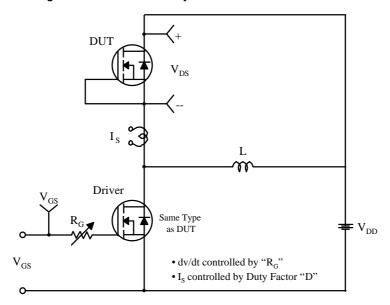
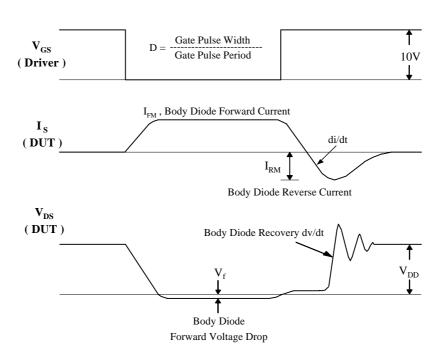


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms







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